

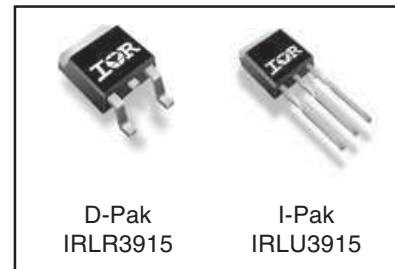
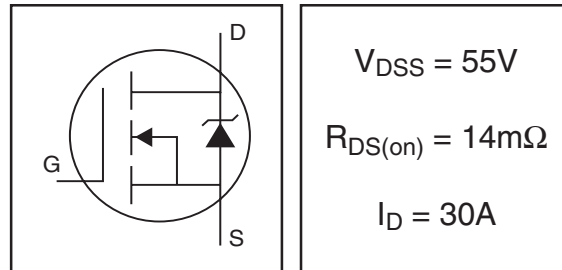
Features

- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this product are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

HEXFET® Power MOSFET



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---------------------------------|---|--------------------------|-------|
| $I_D @ T_C = 25^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon limited) | 61 | A |
| $I_D @ T_C = 100^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ (See Fig.9) | 43 | |
| $I_D @ T_C = 25^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Package limited) | 30 | |
| I_{DM} | Pulsed Drain Current ① | 240 | |
| $P_D @ T_C = 25^\circ\text{C}$ | Power Dissipation | 120 | W |
| | Linear Derating Factor | 0.77 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 16 | V |
| E_{AS} | Single Pulse Avalanche Energy② | 200 | mJ |
| E_{AS} (6 sigma) | Single Pulse Avalanche Energy Tested Value③ | 600 | |
| I_{AR} | Avalanche Current④ | See Fig.12a, 12b, 15, 16 | A |
| E_{AR} | Repetitive Avalanche Energy⑤ | | mJ |
| T_J | Operating Junction and | -55 to + 175 | °C |
| T_{STG} | Storage Temperature Range | | |
| | Soldering Temperature, for 10 seconds | 300 (1.6mm from case) | |

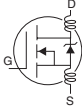
Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|----------------------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case | — | 1.3 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB mount)⑥ | — | 50 | |
| $R_{\theta JA}$ | Junction-to-Ambient— | 110 | | |

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--------------------------------------|--------------------------------------|------|-------|------|-------|--|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 55 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS/ΔT_J} | Breakdown Voltage Temp. Coefficient | — | 0.057 | — | V/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 12 | 14 | mΩ | V _{GS} = 10V, I _D = 30A ④ |
| | | — | 14 | 17 | | V _{GS} = 5.0V, I _D = 26A ④ |
| V _{GS(th)} | Gate Threshold Voltage | 1.0 | — | 3.0 | V | V _{DS} = 10V, I _D = 250μA |
| g _{fs} | Forward Transconductance | 42 | — | — | S | V _{DS} = 25V, I _D = 30A |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 20 | μA | V _{DS} = 55V, V _{GS} = 0V |
| | | — | — | 250 | | V _{DS} = 55V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 200 | nA | V _{GS} = 16V |
| | Gate-to-Source Reverse Leakage | — | — | -200 | | V _{GS} = -16V |
| Q _g | Total Gate Charge | — | 61 | 92 | nC | I _D = 30A |
| Q _{gs} | Gate-to-Source Charge | — | 9.0 | 14 | | V _{DS} = 44V |
| Q _{gd} | Gate-to-Drain ("Miller") Charge | — | 17 | 25 | | V _{GS} = 10V ④ |
| t _{d(on)} | Turn-On Delay Time | — | 7.4 | — | ns | V _{DD} = 28V |
| t _r | Rise Time | — | 51 | — | | I _D = 30A |
| t _{d(off)} | Turn-Off Delay Time | — | 83 | — | | R _G = 8.5Ω |
| t _f | Fall Time | — | 100 | — | | V _{GS} = 10V ④ |
| L _D | Internal Drain Inductance | — | 4.5 | — | nH | Between lead, 6mm (0.25in.) from package and center of die contact |
| L _S | Internal Source Inductance | — | 7.5 | — | |  |
| C _{iss} | Input Capacitance | — | 1870 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 390 | — | | V _{DS} = 25V |
| C _{rss} | Reverse Transfer Capacitance | — | 74 | — | | f = 1.0MHz, See Fig. 5 |
| C _{oss} | Output Capacitance | — | 2380 | — | | V _{GS} = 0V, V _{DS} = 1.0V, f = 1.0MHz |
| C _{oss} | Output Capacitance | — | 290 | — | | V _{GS} = 0V, V _{DS} = 44V, f = 1.0MHz |
| C _{oss eff.} | Effective Output Capacitance ④ | — | 540 | — | | V _{GS} = 0V, V _{DS} = 0V to 44V |

Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|---|--|------|------|-------|---|
| I _S | Continuous Source Current (Body Diode) | — | — | 61 | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 240 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.3 | V | T _J = 25°C, I _S = 30A, V _{GS} = 0V ④ |
| t _{rr} | Reverse Recovery Time | — | 62 | 93 | ns | T _J = 25°C, I _F = 30A, V _{DD} = 25xjkl V |
| Q _{rr} | Reverse Recovery Charge | — | 110 | 170 | nC | di/dt = 100A/μs ④ |
| t _{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D) | | | | |

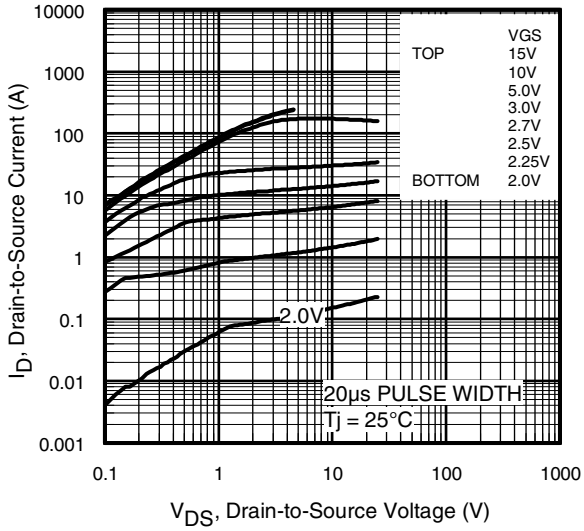


Fig 1. Typical Output Characteristics

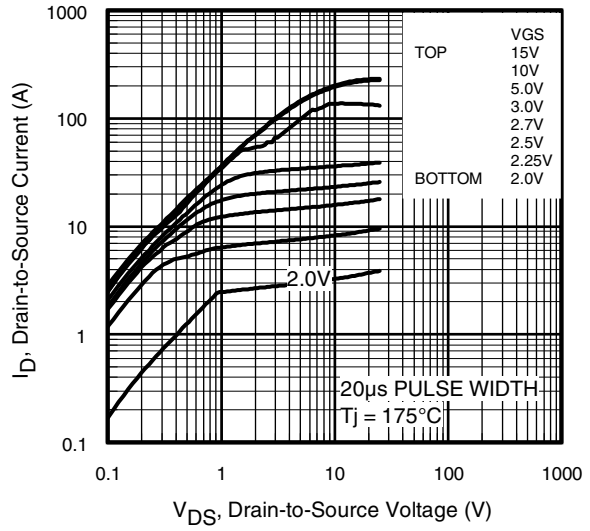


Fig 2. Typical Output Characteristics

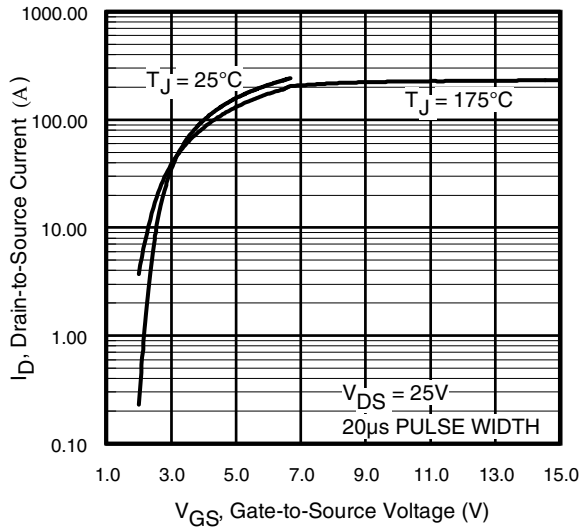


Fig 3. Typical Transfer Characteristics

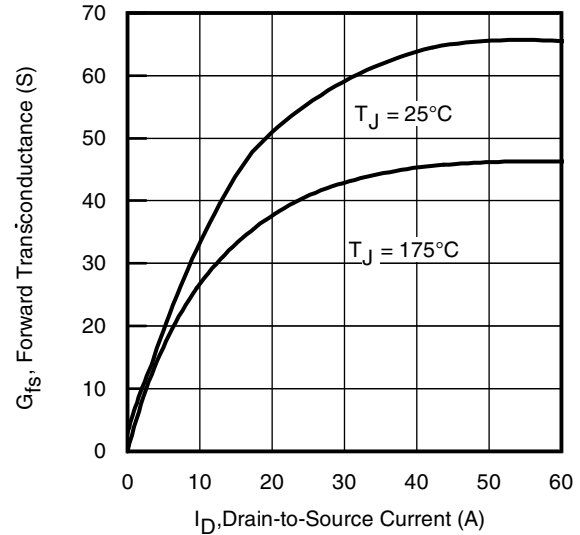


Fig 4. Typical Forward Transconductance vs. Drain Current

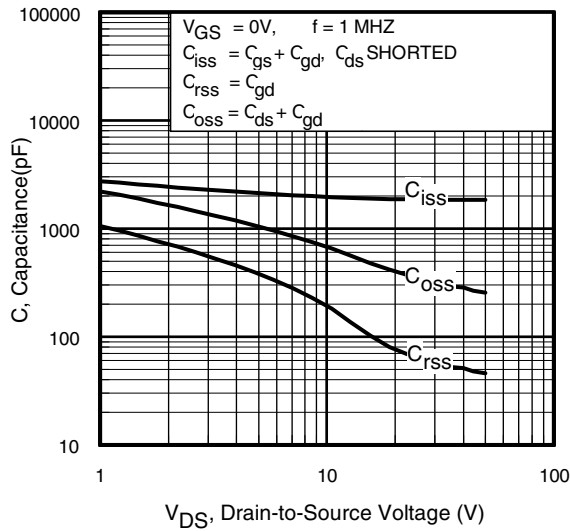


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

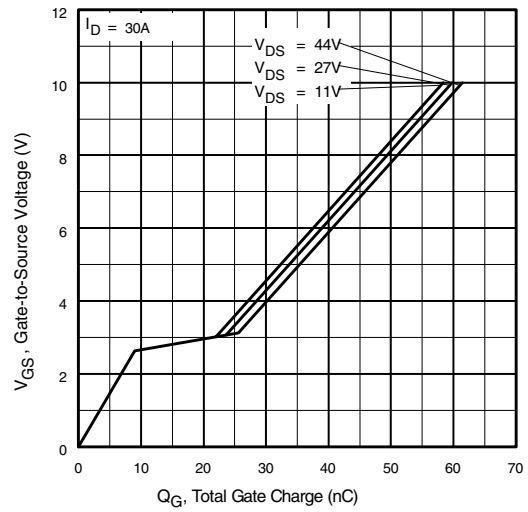


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

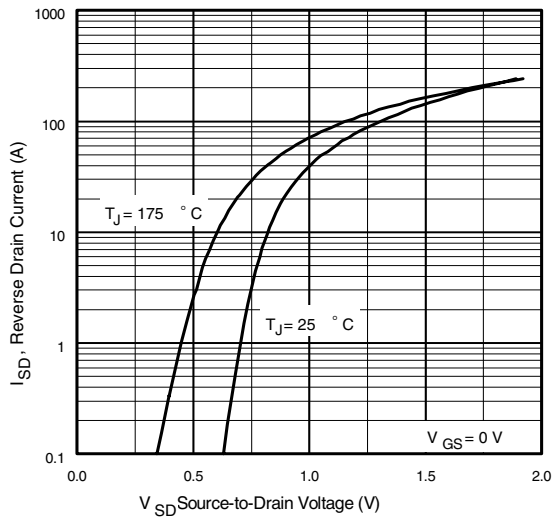


Fig 7. Typical Source-Drain Diode Forward Voltage

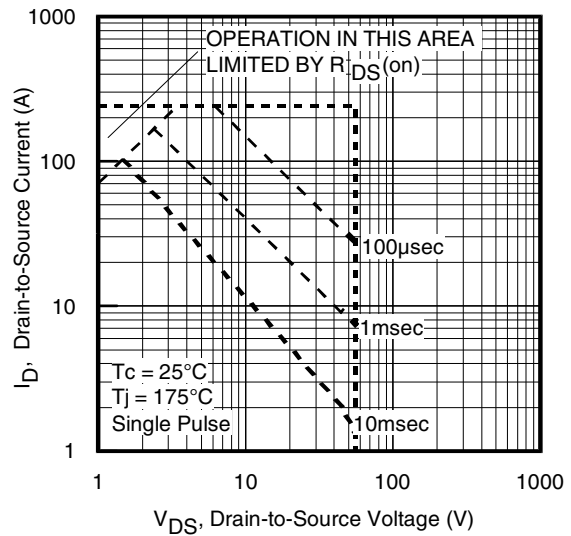


Fig 8. Maximum Safe Operating Area

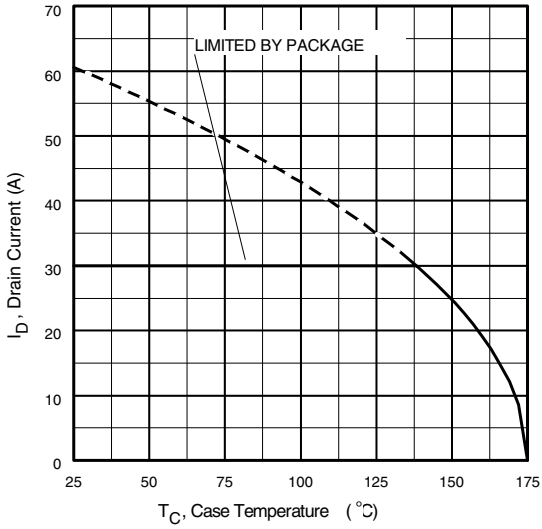


Fig 9. Maximum Drain Current vs. Case Temperature

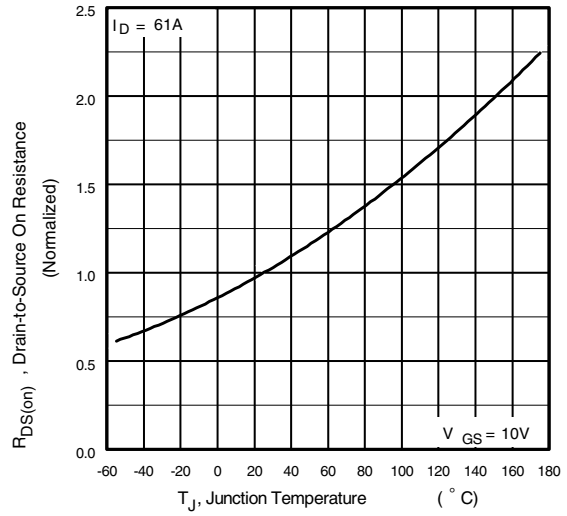


Fig 10. Normalized On-Resistance vs. Temperature

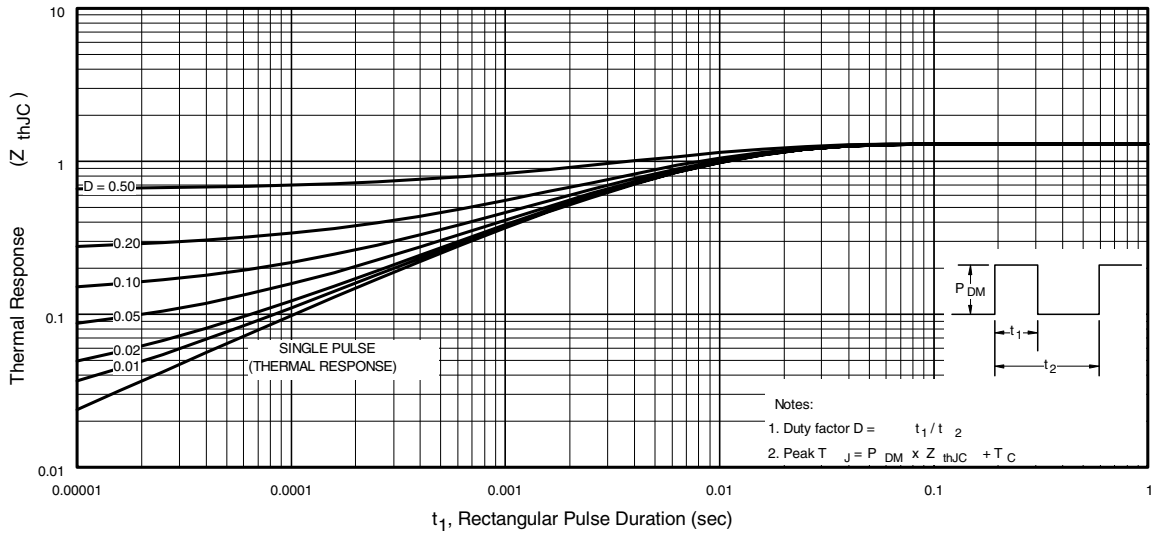


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

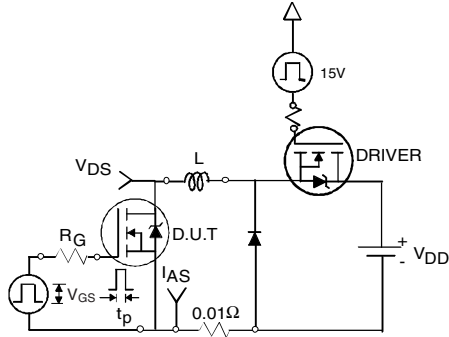


Fig 12a. Unclamped Inductive Test Circuit

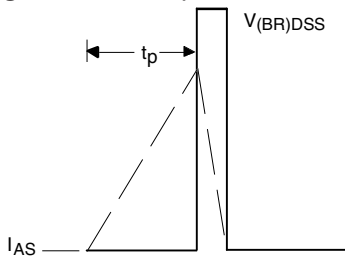


Fig 12b. Unclamped Inductive Waveforms

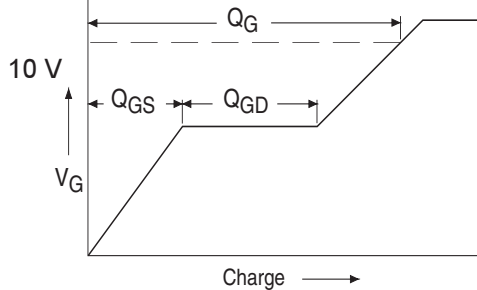


Fig 13a. Basic Gate Charge Waveform

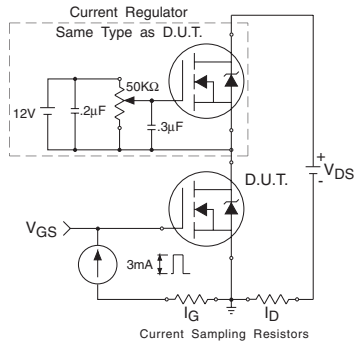


Fig 13b. Gate Charge Test Circuit

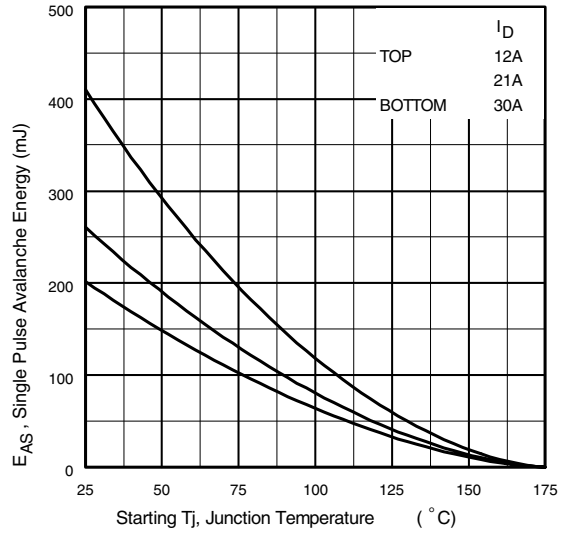


Fig 12c. Maximum Avalanche Energy vs. Drain Current

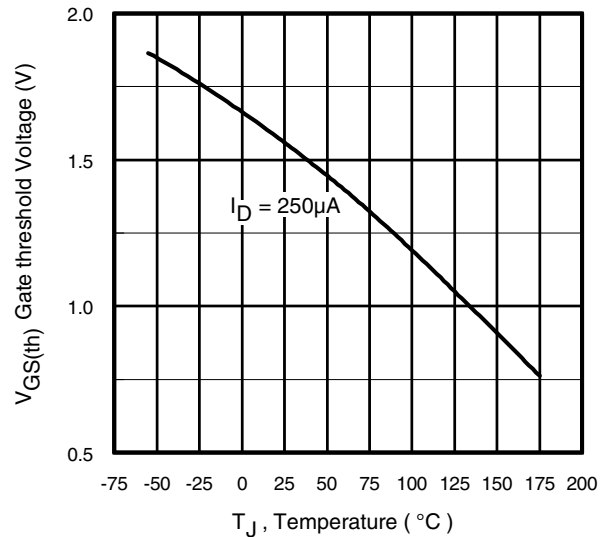


Fig 14. Threshold Voltage vs. Temperature

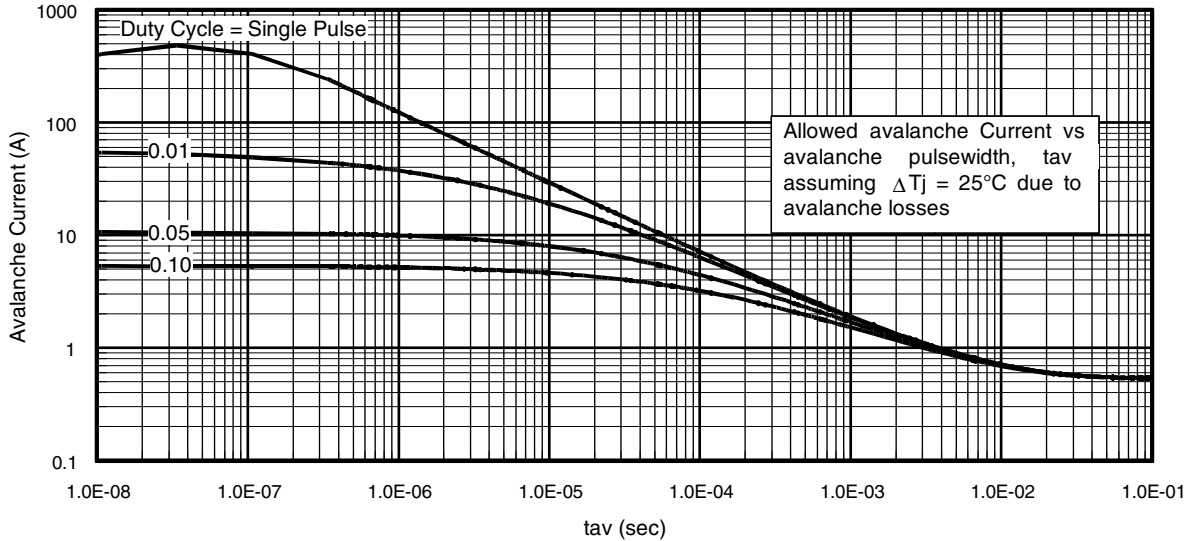


Fig 15. Typical Avalanche Current vs.Pulsewidth

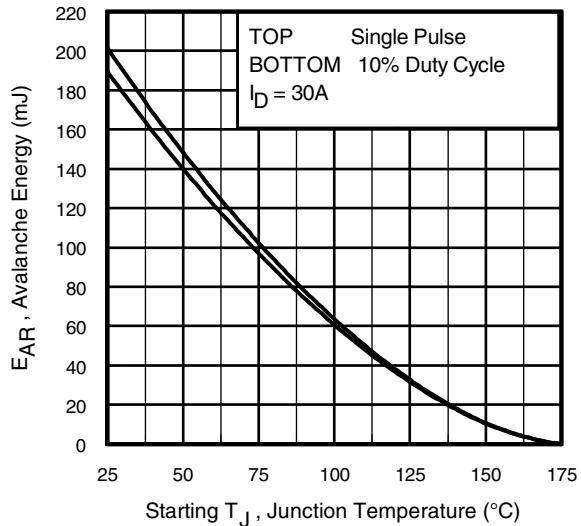


Fig 16. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

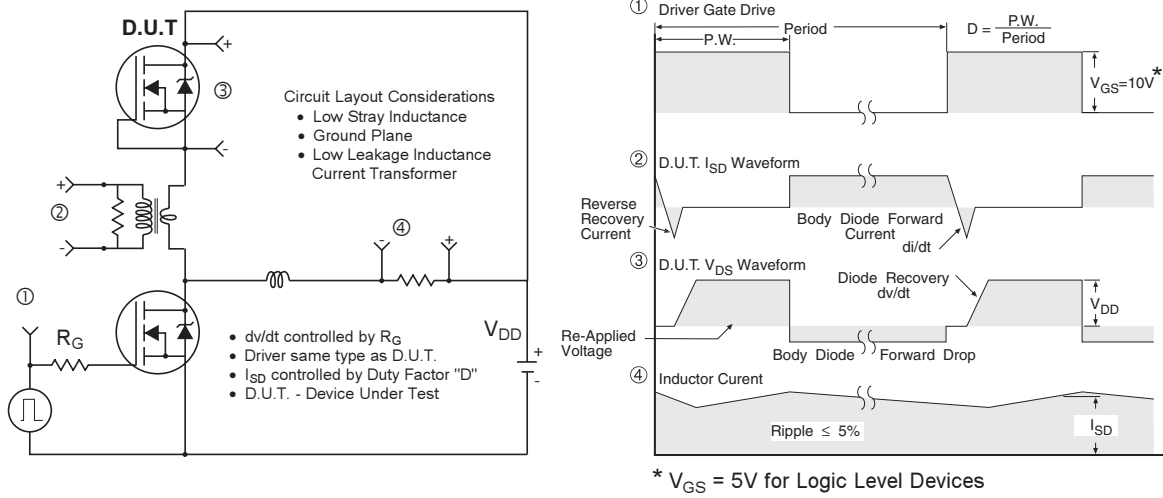


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

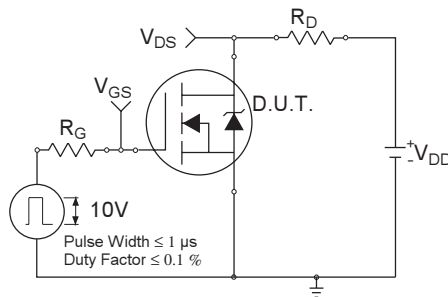


Fig 18a. Switching Time Test Circuit

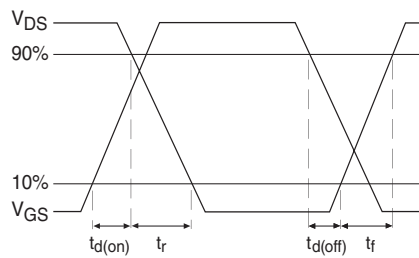
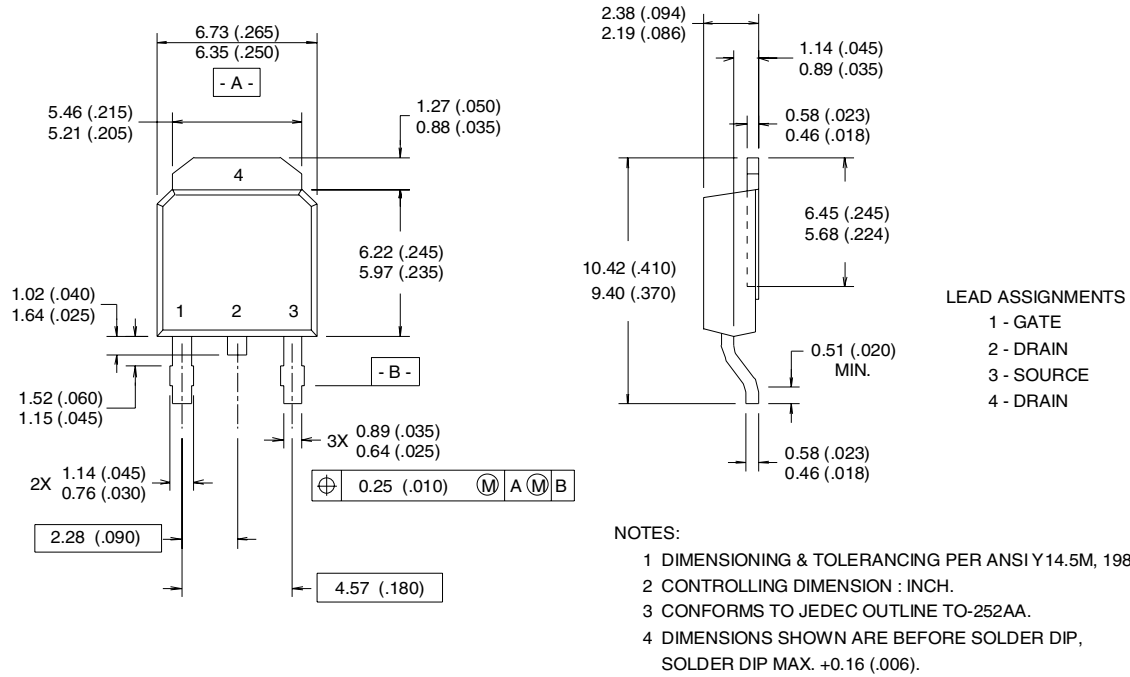


Fig 18b. Switching Time Waveforms

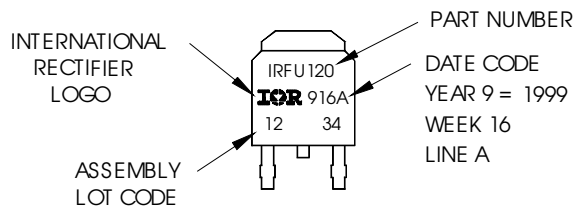
D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
 WITH ASSEMBLY
 LOT CODE 1234
 ASSEMBLED ON WW 16, 1999
 IN THE ASSEMBLY LINE "A"

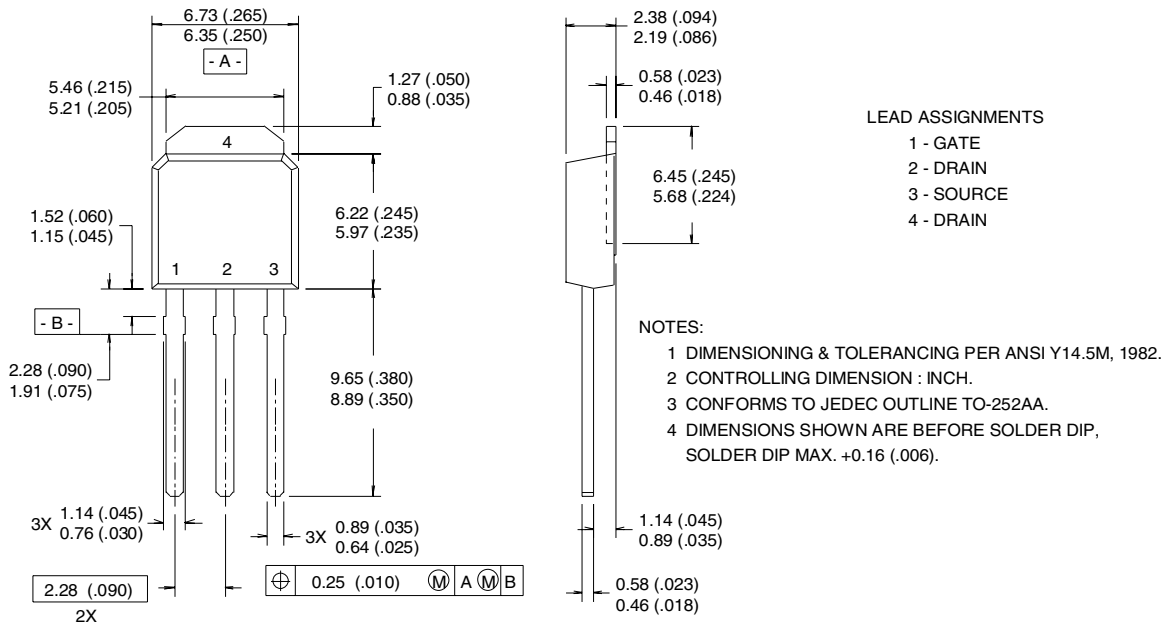


IRLR/U3915



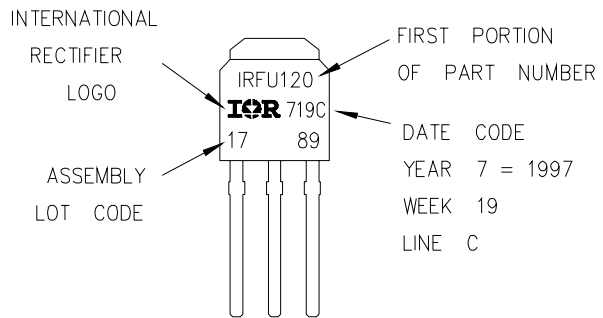
I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



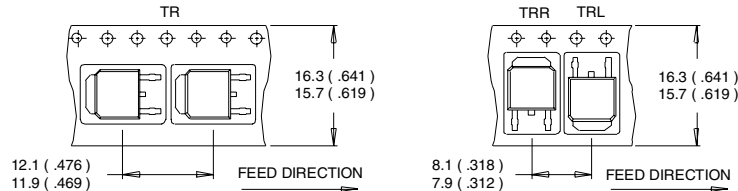
I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"

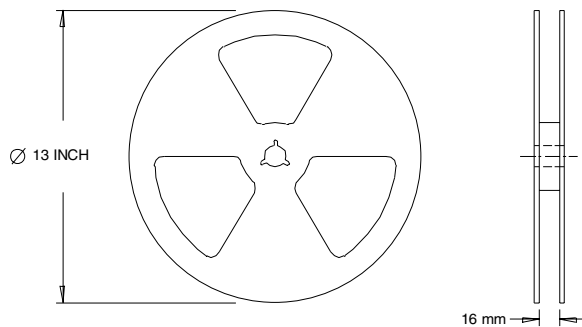


D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.45\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 30\text{A}$, $V_{GS} = 10\text{V}$. Part not recommended for use above this value.
- ③ $I_{SD} \leq 30\text{A}$, $di/dt \leq 280\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 1.0\text{ms}$; duty cycle $\leq 2\%$.
- ⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑦ This value determined from sample failure population. 100% tested to this value in production.
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Automotive [Q101] market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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Visit us at www.irf.com for sales contact information. 09/02

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>